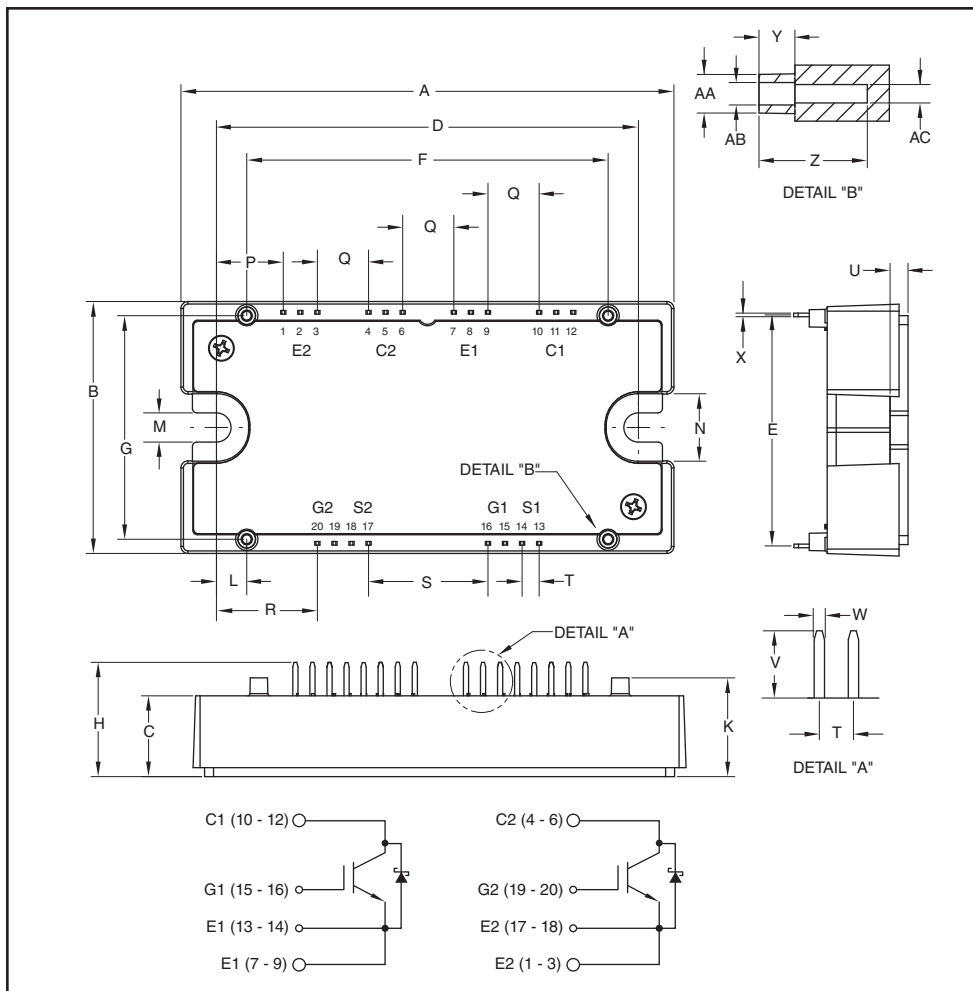


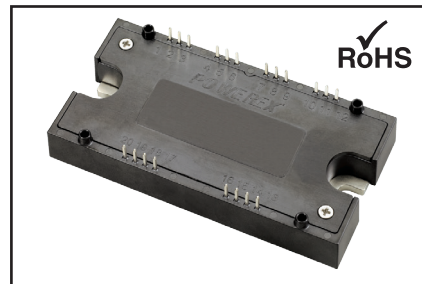
## Split Dual Si/SiC Hybrid IGBT Module 150 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.32	109.8
B	2.21	56.1
C	0.71	18.0
D	3.70±0.02	94.0±0.5
E	2.026	51.46
F	3.17	80.5
G	1.96	49.8
H	1.00	25.5
K	0.87	22.0
L	0.266	6.75
M	0.26	6.5
N	0.59	15.0
P	0.586	14.89

Dimensions	Inches	Millimeters
Q	0.449	11.40
R	0.885	22.49
S	1.047	26.6
T	0.15	3.80
U	0.16	4.0
V	0.30	7.5
W	0.045	1.15
X	0.03	0.8
Y	0.16	4.0
Z	0.47	12.1
AA	0.17 Dia.	4.3 Dia.
AB	0.10 Dia.	2.5 Dia.
AC	0.08 Dia.	2.1 Dia.



### Description:

Powerex IGBT Modules are designed for use in high frequency applications; upwards of 30 kHz for hard switching applications and 80 kHz for soft switching applications. Each module consists of two IGBT Transistors with each transistor having a reverse-connected super-fast recovery free-wheel silicon carbide Schottky diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

### Features:

- ☐ Low ESW(off)
- ☐ Aluminum Nitride Isolation
- ☐ **Discrete Super-Fast Recovery Free-Wheel Silicon Carbide Schottky Diode**
- ☐ Low Internal Inductance
- ☐ 2 Individual Switches per Module
- ☐ Isolated Baseplate for Easy Heat Sinking
- ☐ Copper Baseplate
- ☐ RoHS Compliant

### Applications:

- ☐ Energy Saving Power Systems such as:  
Fans; Pumps; Consumer Appliances
- ☐ High Frequency Type Power Systems such as:  
UPS; High Speed Motor Drives; Induction Heating; Welder; Robotics
- ☐ High Temperature Power Systems such as:  
Power Electronics in Electric Vehicle and Aviation Systems

**QID1215005**
**Split Dual Si/SiC Hybrid IGBT Module**

150 Amperes/1200 Volts

**Absolute Maximum Ratings,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Ratings	Symbol	QID1215003	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 150	$^\circ\text{C}$
Collector-Emitter Voltage (G-E Short)	$V_{CES}$	1200	Volts
Gate-Emitter Voltage (C-E Short)	$V_{GES}$	$\pm 20$	Volts
Collector Current ( $T_C = 25^\circ\text{C}$ )	$I_C$	150*	Amperes
Peak Collector Current	$I_{CM}$	300*	Amperes
Emitter Current** ( $T_C = 25^\circ\text{C}$ )	$I_E$	150*	Amperes
Repetitive Peak Emitter Current ( $T_C = 25^\circ\text{C}$ )**	$I_{EM}$	300*	Amperes
Maximum Collector Dissipation ( $T_C = 25^\circ\text{C}$ , $T_j \leq 150^\circ\text{C}$ )	$P_C$	960	Watts
Mounting Torque, M6 Mounting	—	40	in-lb
Weight	—	270	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{ISO}$	2500	Volts

**IGBT Electrical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current		$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current		$I_{GES}$	$V_{GE} = V_{GES}$ , $V_{CE} = 0V$	—	—	0.5	$\mu A$
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	$I_C = 15mA$ , $V_{CE} = 10V$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 150A$ , $V_{GE} = 15V$ , $T_j = 25^{\circ}C$	—	5.0	6.5	Volts
			$I_C = 150A$ , $V_{GE} = 15V$ , $T_j = 125^{\circ}C$	—	5.0	—	Volts
Total Gate Charge		$Q_G$	$V_{CC} = 600V$ , $I_C = 150A$ , $V_{GE} = 15V$	—	680	—	nC
Input Capacitance		$C_{ies}$	$V_{CE} = 10V$ , $V_{GE} = 0V$	—	—	24	nf
Output Capacitance		$C_{oes}$		—	—	2.0	nf
Reverse Transfer Capacitance		$C_{res}$		—	—	0.45	nf
Inductive	Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V$ , $I_C = 150A$ ,	—	—	TBD	ns
Load	Rise Time	$t_r$	$V_{GE1} = V_{GE2} = 15V$ ,	—	—	TBD	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	$R_G = 2.1\Omega$ ,	—	—	TBD	ns
Time	TimeFall Time	$t_f$	Inductive Load Switching Operation	—	—	TBD	ns

\* Pulse width and repetition rate should be such that device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector silicon carbide Schottky diode (FWDI).

**QID1215005****Split Dual Si/SiC Hybrid IGBT Module**

150 Amperes/1200 Volts

**Reverse Schottky Diode Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Diode Forward Voltage	$V_{FM}$	$I_F = 150\text{A}$ , $V_{GE} = -5\text{V}$	—	1.45	1.75	Volts
		$I_F = 150\text{A}$ , $V_{GE} = -5\text{V}$ , $T_j = 175^\circ\text{C}$	—	1.95	2.35	Volts
Diode Reverse Current	$I_R$	$V_R = 1200\text{V}$	—	1.8	10	mA
		$V_R = 1200$ , $T_j = 175^\circ\text{C}$	—	12	66.6	mA
Diode Capacitive Charge	$Q_C$	$V_R = 1200\text{V}$ , $I_F = 150\text{A}$ , $di/dt = 2200\text{A}/\mu\text{s}$	—	600	—	nC

**Thermal and Mechanical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

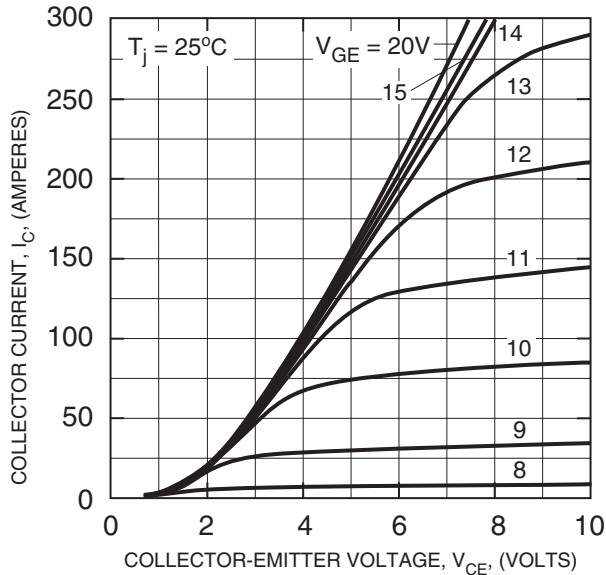
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module, $T_C$ Reference Point Under Chips	—	—	0.13	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module, $T_C$ Reference $T_C$ Reference Point Under Chips	—	—	0.25	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/2 Module, Thermal Grease Applied	—	0.04	—	$^\circ\text{C}/\text{W}$
External Gate Resistance	$R_G$		3.1	—	31	$\Omega$
Internal Inductance	$L_{int}$	IGBT Part	—	10	—	nH

QID1215005

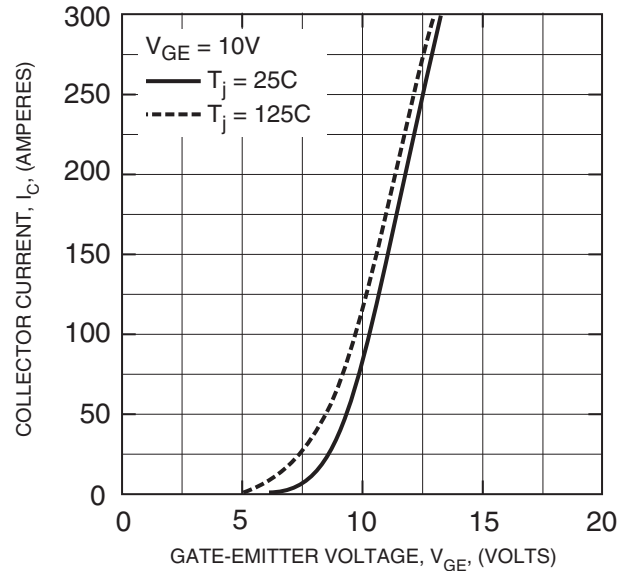
Split Dual Si/SiC Hybrid IGBT Module

150 Amperes/1200 Volts

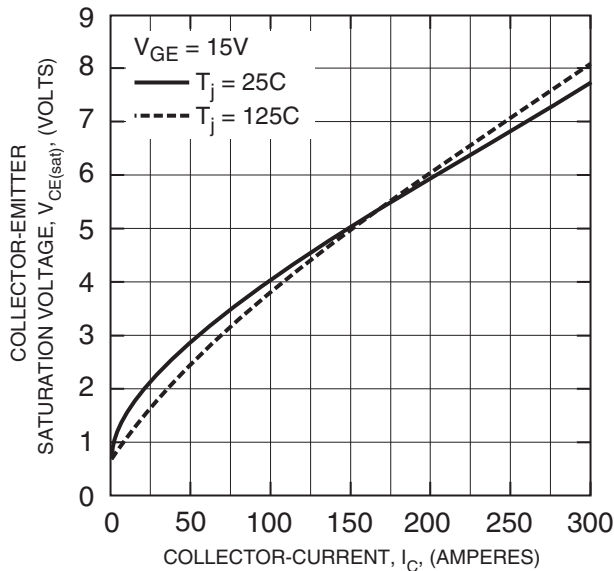
OUTPUT CHARACTERISTICS  
(TYPICAL)



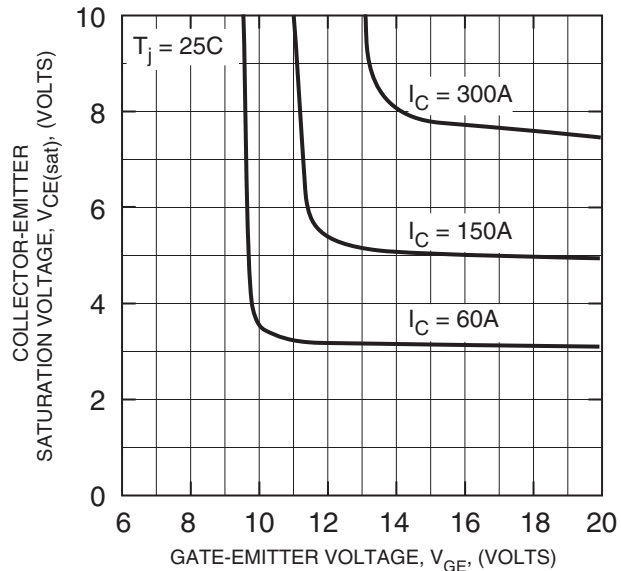
TRANSFER CHARACTERISTICS  
(TYPICAL)



COLLECTOR-EMITTER  
SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)



COLLECTOR-EMITTER  
SATURATION VOLTAGE CHARACTERISTICS  
(TYPICAL)

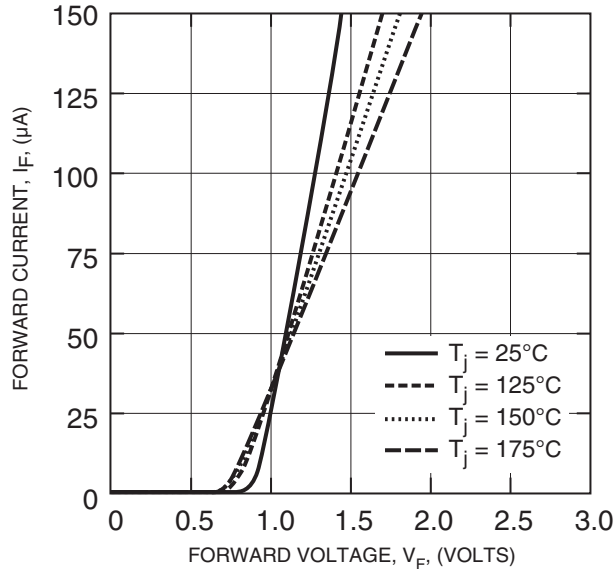


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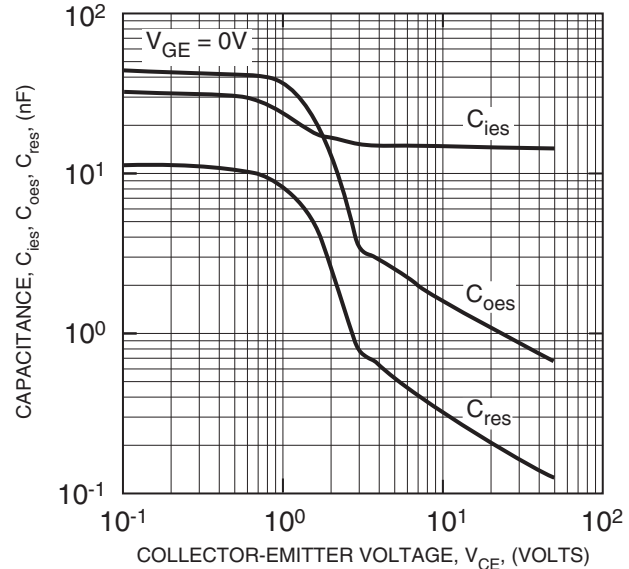
Split Dual Si/SiC Hybrid IGBT Module

150 Amperes/1200 Volts

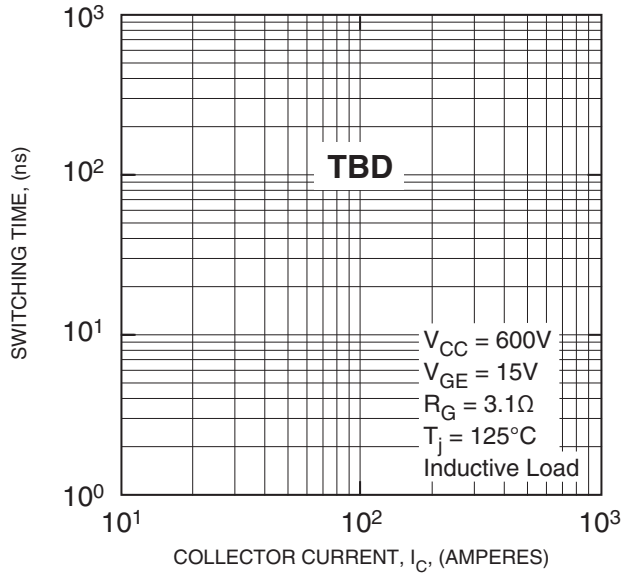
**FREE-WHEEL SCHOTTKY DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)**



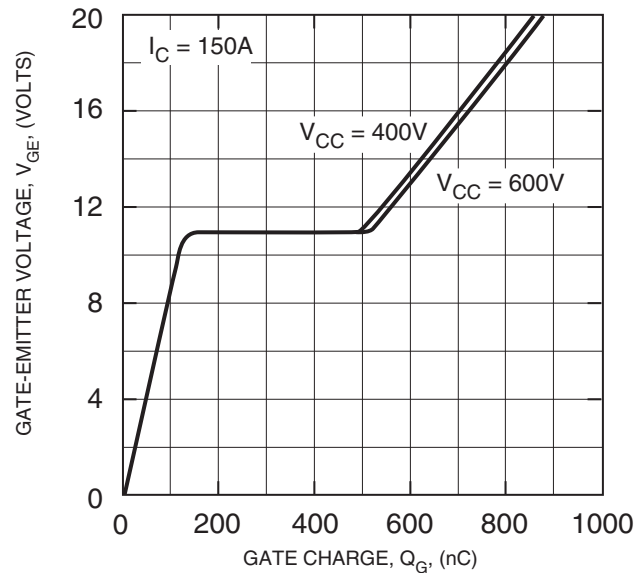
**CAPACITANCE VS.  $V_{CE}$   
(TYPICAL)**



**HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)**



**GATE CHARGE VS.  $V_{GE}$**

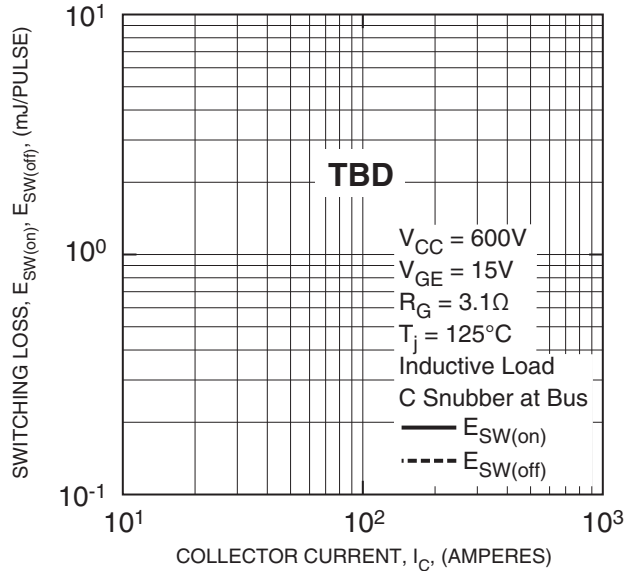


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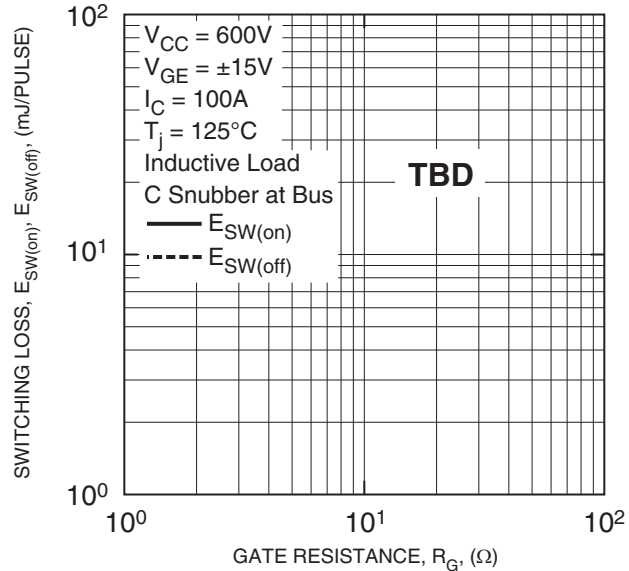
Split Dual Si/SiC Hybrid IGBT Module

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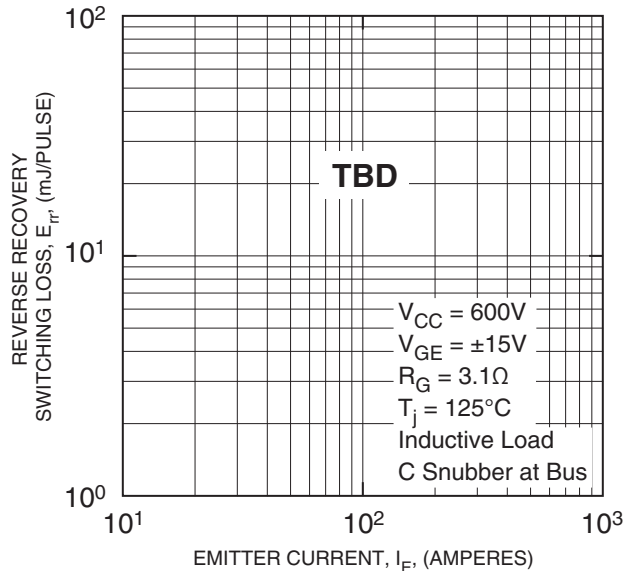
SWITCHING LOSS VS.  
COLLECTOR CURRENT  
(TYPICAL)



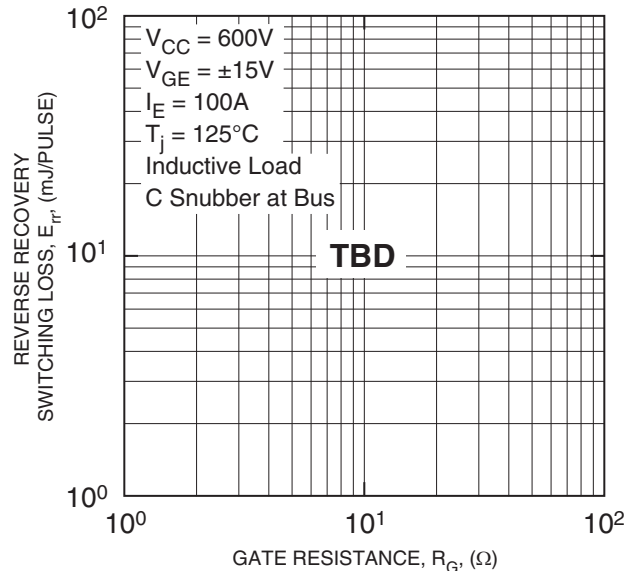
SWITCHING LOSS VS.  
GATE RESISTANCE  
(TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS.  
EMITTER CURRENT  
(TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS.  
GATE RESISTANCE  
(TYPICAL)



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Split Dual Si/SiC Hybrid IGBT Module

150 Amperes/1200 Volts

